

A1 cont  
4. (Amended) A photomask according to claim 2, wherein a difference of a step, between said phase shift pattern and said transparent substrate at said end section of said phase shift pattern that is contacted to said transparent substrate, gradually decreases, the gradual decrease formed by chemical and mechanical polishing.

✓ ✓  
[Claim 5, line 7, change "flat" to --planarized--].

A2  
6. (Amended) A photomask according to claim 5, wherein a thickness of an end section of said phase shift pattern contacted to said transparent substrate gradually decreases, the gradual decrease formed by chemical and mechanical polishing.

✓ ✓  
Claim 7, line 7, change "on" to --by--.

SUB D3  
A3  
8. (Amended) A photomask according to claim 7, wherein an end section of said phase shift pattern that is contacted to said transparent substrate has a sloped shape that gradually decreases, the sloped shape formed by chemical and mechanical polishing.

9. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of a Levenson's type] formed every other opening on the photomask.

A3  
cont

10. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of an auxiliary shifter type] having a auxiliary opening with a shifter which is not resolved adjacent to a main opening.

11. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of an edge highlighting type] formed at an edge of a main opening.

12. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of a half tone type] having a mask pattern formed with a half tone film having a low transmissivity in reverse phase.

SUB C3

13. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of a half tone type with] having a mask pattern formed with a half time film having a low transmissivity in reverse phase and a shade pattern is applied to a large area section.

SUB DA

14. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of a shifter shading type with a shade pattern] having a shade pattern formed with a phase shifter.

A3  
Con 4  
sub 4

15. (Amended) A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern [of an intermediate phase type] having a shade pattern formed with a phase shifter and the shade pattern is applied to a large area section.

[Claim 20, line 16, after "a" insert --planarized--.]

--27. A photomask according to claim 2, wherein said phase shift pattern includes a phase shift pattern having a intermediate phase formed by a shifter in multiple steps.

a4  
sub B2

28. A photomask comprising:  
a transparent substrate;  
a hollow section formed on a surface of said transparent substrate; and  
a shade pattern including a shade section, said shade section made up of a shade film and formed in said hollow section.--

#### REMARKS

This amendment responds to the Office Action dated May 24, 2000 in which the Examiner required affirmation of the telephone election, rejected claims 3, 4, 6 and 8-15 under 35 U.S.C. § 112 second paragraph, rejected claims 1, 2, 5, 7, 9-11, 14, 20 and 22 under 35 U.S.C. § 102(b), rejected claims 1, 2, 5, 7, 9-11 and 14 under 35 U.S.C. § 102(e) and rejected claims 3, 4, 6, 8, 12, 13, 15, 16, 17-19, 21, 23 and 24 under 35 U.S.C. § 103.